(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
21 May 2004 (21.05.2004)

PCT

(10) International Publication Number
WO 2004/042827 A1

(51) International Patent Classification[7]: H01L 29/786

(21) International Application Number:
PCT/US2003/031011

(22) International Filing Date:
24 September 2003 (24.09.2003)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
0211793 24 September 2002 (24.09.2002) FR

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(81) Designated States *(national)*: AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NI, NO, NZ, OM, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, TJ, TM, TN, TR, TT, TZ, UA, UG, UZ, VC, VN, YU, ZA, ZM, ZW.

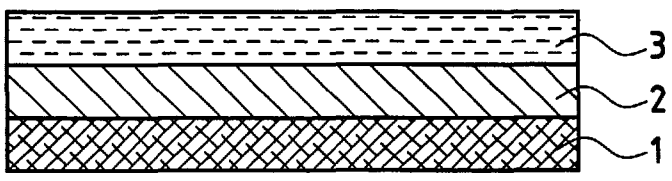
(84) Designated States *(regional)*: European patent (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PT, SE, SI, SK, TR).

Published:
— *with international search report*

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

WO 2004/042827 A1

(54) Title: A SILICON THIN FILM TRANSISTOR, A METHOD OF MANUFACTURE, & A DISPLAY SCREEN



(57) Abstract: In a first aspect, the present invention provides a silicon thin film transistor which comprises: - a substrate; - a barrier layer of porous silica (SiO_2) deposited directly on the substrate; and - a thin layer of silicon that has been caused to be polycrystalline deposited directly on the barrier layer. The invention also provides a method of manufacturing such a transistor, a display screen including such a transistor, and a method of manufacturing such a display screen.